

a plurality of bonding wires electrically connecting said bonding pads with tips of said conductors respectively; and

a resin body sealing said semiconductor chip and said plurality of bonding wires;

wherein a pitch between first ones of adjacent bonding pads at each of four corners defined by the four sides of said main surface of said semiconductor chip is wider than a pitch between second ones of adjacent bonding pads which are disposed at other than the four corners and at a relatively central position of each of the four sides.

8. A semiconductor device according to claim 7, wherein said semiconductor chip is bonded to said substrate by a thermosetting resin.

9. A semiconductor device according to claim 7, wherein said substrate includes an insulating layer formed on said one surface thereof.

10. A semiconductor device according to claim 9, wherein said conductors are formed on said insulating layer of said substrate.

11. A semiconductor device according to claim 7, wherein said conductors are formed of a material having copper as a principal component thereof.

12. A semiconductor device comprising;  
a substrate;  
a semiconductor chip mounted on one surface of said substrate, said

semiconductor chip having an integrated circuit and bonding pads formed on a main surface thereof, said main surface of said semiconductor chip having a quadrilateral shape, said bonding pads being disposed along four sides of said main surface of said semiconductor chip;

a plurality of conductors being disposed on said one surface of said substrate to surround said semiconductor chip along the four sides thereof;

a plurality of bonding wires electrically connecting said bonding pads with tips of said conductors respectively; and

a resin body sealing said semiconductor chip and said plurality of bonding wires;

wherein said bonding pads include first adjacent bonding pads disposed at each of four corners defined by the four sides of said main surface of said semiconductor chip and second adjacent bonding pads disposed at areas of the four sides of said semiconductor chip which are farther from the four corners than said first adjacent bonding pads; and

wherein a pitch between said first adjacent bonding pads is wider than a pitch between said second adjacent bonding pads.

13. A semiconductor device according to claim 12, wherein said semiconductor chip is bonded to said substrate by a thermosetting resin.

14. A semiconductor device according to claim 12, wherein said substrate includes an insulating layer formed on said one surface thereof.

15. A semiconductor device according to claim 14, wherein said conductors are formed on said insulating layer of said substrate.

16. A semiconductor device according to claim 12, wherein said conductors are formed of a material having copper as a principal component thereof.